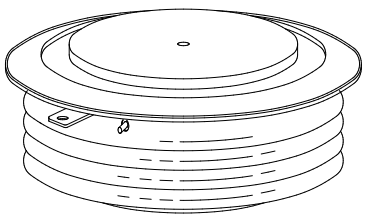
****

T8C



Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK1100/25	2500	2500	2700
KK1100/28	2800	2800	3000

V_{RRM} = Repetitive peak reverse voltage
V_{DRM} = Repetitive peak off state voltage
V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	5 mA 100 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/μs

Notes
All ratings are specified for Tj=25 °C unless otherwise stated.
(1) All voltage ratings are specified for an applied 50Hz/60zHz sinusoidal waveform over the temperature range 0 to +125 °C
(2) 10 msec. Max. Pulse width
(3) Maximum value for Tj=125 °C.
(4) Minimum value for linear and exponential waveshape to 67% rated $V_{DRM.}$ Gate open, Tj=125 °C
(5) The value of di/dt is established in accordance with JB/T4193-2013.

Average value of on-state current	$I_{T(AV)}$		1100		A	Sinewave,180° conduction,Tc=55°C
RMS value of on-state current	I_{TRMS}		1727		A	Nominal value
Peak one cycle surge (non repetitive) current	I_{TSM}		14400		A	10 msec (50Hz), sinusoidal wave-shape, 180° conduction, T_j = 125 °C
I square t	I^2t		$1.04x10^6$		A^2s	10 msec
Latching current	I_L		1000		mA	V_D=12V; R_L=12ohms
Holding current	I_H		200		mA	V_D=12V; I=2.5A
Peak on-state voltage	V_{TM}		2.8		V	I_{TM}= 3000A;Tj =25°C
Threshold voltage, low-level	V_{TO}		1.51		V	Tj=125°C
Slope resistance, low-level	r_T		0.43		mΩ	1000A to 2500A
Critical rate of rise of on-state current(5)	di/dt		200		A/μs	Tj=125°C; V_D = 0.67 V_{DRM}; f=50Hz; I_{TM}=2000A

Peak gate power dissipation	5

